L Number	Hits	Search Text	DB	Time stamp
I	6802	257/173,328,355-363,546,758.ccls.	USPAT;	2004/04/16 18:20
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	2004/04/17 10 21
2	1004	438/212,268,309.ccls.	USPAT;	2004/04/16 18:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	7712	257/172 200 255 262 546 759 colo or 429/212 269 200 colo	IBM_TDB USPAT;	2004/04/16 18:21
3	7713	257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.	US-PGPUB;	200 4 /04/10 18.21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
4	4176	(257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and	USPAT;	2004/04/16 19:13
4	4170	(semiconductor near (layer substrate))	US-PGPUB;	200 110 110 17110
		(Semiconductor near (layer substrate))	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
5	2887	((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and	USPĀT;	2004/04/16 19:14
		(semiconductor near (layer substrate))) and (source drain)	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
6	2154	(((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and	USPAT;	2004/04/16 19:14
		(semiconductor near (layer substrate))) and (source drain)) and (gate	US-PGPUB;	
		near (insulat\$3 oxide electrode))	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	2004/04/17 10:00
7	727	((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and	USPAT;	2004/04/16 19:09
-		(semiconductor near (layer substrate))) and (source drain)) and (gate	US-PGPUB;	
		near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3)	EPO; JPO;	
			DERWENT; IBM TDB	
	1.42	((((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and	USPAT;	2004/04/16 19:10
8	143	(((((23/17/3,328,333-303,340,738.ccis. of 436/212,206,307.ccis.) and (semiconductor near (layer substrate))) and (source drain)) and (gate	US-PGPUB;	2004/04/10 17:10
		near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3)) and	ЕРО; ЛРО;	
		electrostatic	DERWENT;	
		·	IBM TDB	
9	3	("5086365" "5963409" "6080612").PN.	USPAT	2004/04/16 18:54
10	9	["4997786" "5534459" "5610790" "5880001" "5897939"	USPAT	2004/04/16 18:54
		"5899714" "5930638" "5953600" "5970333").PN.		
11	11	("4609931" "4616243" "4692834" "4745450" "5124578"	USPAT ·	2004/04/16 18:56
		"5272586" "5287241" "5440162" "5479039" "5498892"		
		"5663678").PN.		
12	727	(((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and	USPAT;	2004/04/16 19:11
		(semiconductor near (layer substrate))) and (source drain)) and (gate	US-PGPUB;	
		near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 IDL)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/04/16 10 11
13	143	(((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and	USPAT;	2004/04/16 19:11
		(semiconductor near (layer substrate))) and (source drain)) and (gate	US-PGPUB;	
		near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3	EPO; JPO; DERWENT;	
	•	IDL)) and electrostatic	IBM TDB	
14	739	((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and	USPAT;	2004/04/16 19:14
14	. 139	((((25//1/3,328,333-303,340,738.ccis. of 438/212,208,309.ccis.) and (semiconductor near (layer substrate))) and (source drain)) and (gate	US-PGPUB;	200 110 17.14
		near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 ILD)	EPO; JPO;	
		(monature original monature monature)	DERWENT;	
			IBM TDB	

15	146	(((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3	USPAT; US-PGPUB; EPO; JPO;	2004/04/16 19:13
		ILD)) and electrostatic	DERWENT; IBM_TDB	
16	341067	257/\$.ccls. 438/\$.ccls.	USPAT; US-PGPUB;	2004/04/16 19:13
			EPO; JPO; DERWENT;	
17	10480	(257/\$.ccls. 438/\$.ccls.) and electrostatic	IBM_TDB USPAT; US-PGPUB;	2004/04/16 19:20
			EPO; JPO; DERWENT; IBM_TDB	
18	8796	((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)	USPAT; US-PGPUB; EPO; JPO;	2004/04/16 19:20
			DERWENT; IBM_TDB	2004/04/15 10:20
19	6392	(((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/16 19:20
20	3295	(((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near	IBM_TDB USPAT;	2004/04/16 19:21
		(layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))	US-PGPUB; EPO; JPO; DERWENT;	
21	1091	(((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 ILD)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/16 19:18
22	3	((((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near	DERWENT; IBM_TDB USPAT;	2004/04/16 19:19
		(layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 ILD)) and ((first near (interlevel ILD))) with (second near (interlevel ILD)))	US-PGPUB; EPO; JPO; DERWENT;	
23	1098	((((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near	IBM_TDB USPAT; US-PGPUB;	2004/04/16 19:21
		(insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)	EPO; JPO; DERWENT; IBM_TDB	
24	3	(((((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)) and ((first near (interlevel ILD)) with (second near (interlevel ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/16 19:19
25	3	((((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near	IBM_TDB USPAT; US-PGPUB;	2004/04/16 19:22
		(insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)) and ((first near (inter\$1level ILD)) with (second near (inter\$1level ILD)))	EPO; JPO; DERWENT; IBM_TDB	
26	267605	electrostatic ESD	USPAT; US-PGPUB; EPO; JPO;	2004/04/16 19:20
			DERWENT; IBM_TDB	

		(1) (1) (1) (1)	TIODATE	2004/04/16 10 20
27	71784	(electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)	USPAT; US-PGPUB;	2004/04/16 19:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
28	39347	((electrostatic ESD) and ((semiconductor near (layer substrate))	USPAT;	2004/04/16 19:39
		substrate)) and (source drain)	US-PGPUB;	
		,	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
29	5862	(((electrostatic ESD) and ((semiconductor near (layer substrate))	USPĀT;	2004/04/16 19:39
2,	3332	substrate)) and (source drain)) and (gate near (insulat\$3 oxide	US-PGPUB;	
		electrode))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
30	1783	(((((electrostatic ESD) and ((semiconductor near (layer substrate))	USPAT;	2004/04/16 19:28
30	1763	substrate)) and (source drain)) and (gate near (insulat\$3 oxide	US-PGPUB;	
		electrode))) and (inter\$11evel\$1 interconnect\$3 ILD)	ЕРО; ЛРО;	
	ļ	electrode))) and (interprevent interconnectes into)	DERWENT;	
			IBM TDB	
21		((((((electrostatic ESD) and ((semiconductor near (layer substrate))	USPAT;	2004/04/16 19:22
31	4	substrate)) and (source drain)) and (gate near (insulat\$3 oxide	US-PGPUB;	200 110 11 10 19.22
		electrode))) and (inter\$1level\$1 interconnect\$3 LD)) and (first near	EPO; JPO;	
			DERWENT;	
	1	(inter\$1level ILD)) with (second near (inter\$1level ILD)))	IBM_TDB	
		(1) (1) 1 (1) (1) (1) (1) (1) (1) (1) (1		2004/04/16 19:24
32	11	((((((electrostatic ESD) and ((semiconductor near (layer substrate))	USPAT;	2004/04/10 17.24
		substrate)) and (source drain)) and (gate near (insulat\$3 oxide	US-PGPUB;	
		electrode))) and (inter\$1level\$1 interconnect\$3 ILD)) and ((first near	ЕРО; ЛРО;	
	ļ	(inter\$1level ILD)) same (second near (inter\$1level ILD)))	DERWENT;	
		(5 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	IBM_TDB	2004/04/16 19:36
33	0	(first near gate near interconnect\$3) with (first near drain near	USPAT;	2004/04/10 19.30
		interconnect\$3)	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
1		(7)	IBM_TDB	2004/04/16 19:26
34	0	(first near gate near interconnect\$3) same (first near drain near	USPAT; US-PGPUB;	2004/04/10 19.20
		interconnect\$3)		
		·	ЕРО; ЛРО;	
			DERWENT;	
	1	100 100	IBM_TDB	2004/04/16 19:26
35	2	(first near gate near interconnect\$3) and (first near drain near	USPAT;	2004/04/10 19.20
		interconnect\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/04/16 19:27
36	253785	((semiconductor near (layer substrate)) substrate) same (source drain)	USPAT;	2004/04/10 19.2/
1			US-PGPUB;	
			ЕРО; ЛРО;	
		· ·	DERWENT;	
l			IBM_TDB	2004/04/16 10:29
37	31265	(((semiconductor near (layer substrate)) substrate) same (source drain))	USPAT;	2004/04/16 19:28
		and ((gate near (insulat\$3 oxide)) with (gate near electrode))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/04/17 10 20
38	5854	(((((semiconductor near (layer substrate)) substrate) same (source drain))	USPAT;	2004/04/16 19:39
		and ((gate near (insulat\$3 oxide)) with (gate near electrode))) and	US-PGPUB;	
		(inter\$1level\$1 interconnect\$3 ILD)	EPO; JPO;	
			DERWENT;	
Ĺ	<u> </u>		IBM_TDB	l

39	186	(gate near interconnect\$3) with (drain near interconnect\$3)	USPAT;	2004/04/16 19:29
			US-PGPUB;	
			EPO, JPO;	
			DERWENT;	
40	46	(((((semiconductor near (layer substrate)) substrate) same (source	IBM_TDB USPAT;	2004/04/16 19:29
40	40	drain)) and ((gate near (insulat\$3 oxide)) with (gate near electrode)))	US-PGPUB;	2004/04/10 17.29
		and (inter\$1level\$1 interconnect\$3 ILD)) and ((gate near	EPO; JPO;	
		interconnect\$3) with (drain near interconnect\$3))	DERWENT;	
			IBM_TDB	
41	0	(first near gate near (contact\$3 interconnect\$3)) with (first near drain	USPĀT;	2004/04/16 19:37
		near (contact3 interconnect\$3))	US-PGPUB;	
			ЕРО; ЛРО;	
	ļ		DERWENT;	
40	107	(to (to to to to to to with (durin moon (contact?	IBM_TDB USPAT;	2004/04/16 19:37
42	197	(gate near (contact\$3 interconnect\$3)) with (drain near (contact3 interconnect\$3))	US-PGPUB;	2004/04/10 19.57
		interconnects(3))	EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
43	23	((gate near (contact\$3 interconnect\$3)) with (drain near (contact3	USPĀT;	2004/04/16 19:49
		interconnect\$3))) and (electrostatic ESD)	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
		(4.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1	IBM_TDB	2004/04/16 10:49
44	158	((gate near (contact\$3 interconnect\$3)) with (drain near (contact3	USPAT; US-PGPUB;	2004/04/16 19:48
		interconnect\$3))) and ((semiconductor near (layer substrate)) substrate)	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
45	158	(((gate near (contact\$3 interconnect\$3)) with (drain near (contact3	USPĀT;	2004/04/16 19:48
		interconnect\$3))) and ((semiconductor near (layer substrate)) substrate))	US-PGPUB;	
		and (source drain)	ЕРО; ЈРО;	
			DERWENT;	
	141	((()	IBM_TDB	2004/04/16 19:48
46	141	((((gate near (contact\$3 interconnect\$3)) with (drain near (contact3 interconnect\$3))) and ((semiconductor near (layer substrate)) substrate))	USPAT; US-PGPUB;	2004/04/10 19.46
		and (source drain)) and (gate near (insulat\$3 oxide electrode))	EPO; JPO;	
		and (source drain)) and (gate near (instatute oxide electrode))	DERWENT;	
			IBM_TDB	
47	141	((((((gate near (contact\$3 interconnect\$3)) with (drain near (contact3	USPAT;	2004/04/16 19:47
		interconnect\$3))) and ((semiconductor near (layer substrate)) substrate))	US-PGPUB;	
		and (source drain)) and (gate near (insulat\$3 oxide electrode))) and	EPO; JPO;	
		(inter\$1level\$1 interconnect\$3 ILD)	DERWENT; IBM TDB	
48	398	(first near (inter\$1level ILD)) with (second near (inter\$1level ILD))	USPAT;	2004/04/16 19:50
48	398	(Hist hear (interprieve ind)) with (second hear (interprieve ind))	US-PGPUB;	2004/04/10 17:50
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
49	374	((first near (inter\$1level ILD)) with (second near (inter\$1level ILD)))	USPAT;	2004/04/16 19:48
		and ((semiconductor near (layer substrate)) substrate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
50	274	((((first near (inter\$1level ILD)) with (second near (inter\$1level ILD)))	USPAT;	2004/04/16 19:48
טכ	2/4	and ((semiconductor near (layer substrate)) substrate)) and (source	US-PGPUB;	200 0 17.10
		drain)	ЕРО; ЈРО;	
		· · · · · · · · · · · · · · · · · · ·	DERWENT,	
			IBM_TDB	

L Number	Hits	Search Text	DB	Time stamp
51	222	((((first near (inter\$1level ILD)) with (second near (inter\$1level ILD)))	USPAT;	2004/04/16 19:49
		and ((semiconductor near (layer substrate)) substrate)) and (source	US-PGPUB;	
		drain)) and (gate near (insulat\$3 oxide electrode))	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
52	4	(((((first near (inter\$1level ILD)) with (second near (inter\$1level ILD)))	USPAT;	2004/04/16 19:49
		and ((semiconductor near (layer substrate)) substrate)) and (source	US-PGPUB;	
		drain)) and (gate near (insulat\$3 oxide electrode))) and (electrostatic	ЕРО; ЈРО;	
		ESD)	DERWENT;	
			IBM_TDB	
53	57	(first near (inter\$1level ILD)) with (second near (inter\$1level ILD))	USPAT,	2004/04/16 19:57
		with (third near (inter\$1level ILD))	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
54	6	((first near (inter\$1level ILD)) with (second near (inter\$1level ILD)))	USPAT;	2004/04/16 20:12
		and ((gate near (interconnect contact wir\$3)) with (drain near	US-PGPUB;	
		(interconnect contact wir\$3)))	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
55	2004	((gate near (interconnect contact wir\$3)) with (drain near (interconnect	USPAT;	2004/04/16 20:13
		contact wir\$3)))	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
56	179	(((gate near (interconnect contact wir\$3)) with (drain near (interconnect	USPAT;	2004/04/16 20:13
		contact wir\$3)))) and (electrostatic ESD)	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	